

John D Cressler

List of Publications by Year in descending order

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1766
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#	ARTICLE	IF	CITATIONS
1	Design Methodology for a Wideband, Low Insertion Loss, Digital Step Attenuator in SiGe BiCMOS Technology. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 744-748.	2.2	5
2	A Millimeter-Wave, Transformer-Based, SiGe Distributed Attenuator. IEEE Microwave and Wireless Components Letters, 2022, 32, 145-148.	2.0	7
3	Response of Integrated Silicon Microwave Diodes to X-Ray and Fast-Neutron Irradiation. IEEE Transactions on Nuclear Science, 2022, 69, 282-289.	1.2	0
4	Modeling Transient Loss Due to Ionizing Particles in Silicon Photonic Waveguides. IEEE Transactions on Nuclear Science, 2022, 69, 518-526.	1.2	1
5	Using Machine Learning to Mitigate Single-Event Upsets in RF Circuits and Systems. IEEE Transactions on Nuclear Science, 2022, 69, 381-389.	1.2	1
6	Single-Event Transients in a Commercially Available, Integrated Germanium Photodiode for Silicon Photonic Systems. IEEE Transactions on Nuclear Science, 2022, 69, 527-533.	1.2	1
7	Total-Ionizing-Dose Response of SiGe HBTs at Elevated Temperatures. IEEE Transactions on Nuclear Science, 2022, 69, 1079-1084.	1.2	1
8	Voltage-Controlled Oscillator Utilizing Inverse-Mode SiGe-HBT Biasing Circuit for the Mitigation of Single-Event Effects. IEEE Transactions on Nuclear Science, 2022, 69, 1242-1248.	1.2	2
9	An Efficient, Broadband SiGe HBT Non-Uniform Distributed Power Amplifier Leveraging a Compact, Two-Section $\lambda/4$ Output Impedance Transformer. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 3524-3533.	2.9	4
10	A Compact, Low Loss, and Broadband Two-Section Lumped-Element Wilkinson Power Combiner Using 130 nm SiGe HBT BiCMOS Technology. , 2022, , .		0
11	Triaxial Balun With Inherent Harmonic Reflection for Millimeter-Wave Frequency Doublers. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 2822-2831.	2.9	8
12	Variability of p-n Junctions and SiGe HBTs at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2021, 68, 987-993.	1.6	5
13	Operation of Current Mirrors in SiGe BiCMOS Technology at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2021, 68, 1439-1445.	1.6	5
14	A New Emitter-Base-Collector-Base-Emitter SiGe HBT for High Power, Single-Pole Double-Throw X-Band Switches. IEEE Electron Device Letters, 2021, 42, 465-468.	2.2	4
15	Integrated Silicon Photonics for Enabling Next-Generation Space Systems. Photonics, 2021, 8, 131.	0.9	18
16	Optical Single-Event Transients Induced in Integrated Silicon-Photonic Waveguides by Two-Photon Absorption. IEEE Transactions on Nuclear Science, 2021, 68, 785-792.	1.2	14
17	Millimeter-Wave SiGe Radiometer Front End With Transformer-Based Dicke Switch and On-Chip Calibration Noise Source. IEEE Journal of Solid-State Circuits, 2021, 56, 1464-1474.	3.5	7
18	Variability in Total-Ionizing-Dose Response of Fourth-Generation SiGe HBTs. IEEE Transactions on Nuclear Science, 2021, 68, 949-957.	1.2	7

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19	A 60-GHz SiGe Power Amplifier With Three-Conductor Transmission-Line-Based Wilkinson Baluns and Asymmetric Directional Couplers. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 709-722.	2.9	9
20	Analysis of the Impact of Radiation-Induced Optical Transients on Deep-Space Optical Communications Systems using PPM. , 2021, , .		0
21	Performance Improvements of Reverse-Saturated SiGe HBT Millimeter-Wave Switches with Floating Emitter Configuration. , 2021, , .		0
22	A 24 GHz SiGe HBT Cascode Non-uniform Distributed Power Amplifier Using A Compact, Wideband Two-Section Lumped Element Output Impedance Transformer. , 2021, , .		4
23	Dynamic Behavior of Breakdown Mechanisms in SiGe HBTs. , 2021, , .		1
24	Dual-Band Millimeter-Wave Quadrature LO Generation With a Common-Centroid Floorplan. IEEE Transactions on Circuits and Systems II: Express Briefs, 2020, 67, 260-264.	2.2	1
25	Response of Waveguide-Integrated Germanium-on-Silicon p-i-n Photodiodes to Neutron Displacement Damage. IEEE Transactions on Nuclear Science, 2020, 67, 296-304.	1.2	6
26	Comparison of Single-Event Transients in SiGe HBTs on Bulk and Thick-Film SOI. IEEE Transactions on Nuclear Science, 2020, 67, 71-80.	1.2	7
27	New Approach for Pulsed-Laser Testing That Mimics Heavy-Ion Charge Deposition Profiles. IEEE Transactions on Nuclear Science, 2020, 67, 81-90.	1.2	16
28	Electronic-to-Photonic Single-Event Transient Propagation in a Segmented Mach-Zehnder Modulator in a Si/SiGe Integrated Photonics Platform. IEEE Transactions on Nuclear Science, 2020, 67, 260-267.	1.2	3
29	Single-Event Transients in SiGe HBTs Induced by Pulsed X-Ray Microbeam. IEEE Transactions on Nuclear Science, 2020, 67, 91-98.	1.2	4
30	A D-band SiGe Frequency Doubler with a Harmonic Reflector Embedded in a Triaxial Balun. , 2020, , .		4
31	Investigation of π -Doubler Technique to Improve RF Performance of Inverse-Mode SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2020, 30, 873-875.	2.0	5
32	A New Wideband, Low Insertion Loss, High Linearity SiGe RF Switch. IEEE Microwave and Wireless Components Letters, 2020, 30, 985-988.	2.0	23
33	Mitigation of Single-Event Effects in SiGe-HBT Current-Mode Logic Circuits. Sensors, 2020, 20, 2581.	2.1	1
34	A Two-Way Wideband Active SiGe BiCMOS Power Divider/Combiner for Reconfigurable Phased Arrays With Controllable Beam Width. IEEE Access, 2020, 8, 2578-2589.	2.6	2
35	Tradeoffs Between RF Performance and SET Robustness in Low-Noise Amplifiers in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2020, 67, 1521-1529.	1.2	3
36	A 60-GHz SiGe Radiometer Calibration Switch Utilizing a Coupled Avalanche Noise Source. IEEE Microwave and Wireless Components Letters, 2020, 30, 417-420.	2.0	18

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37	Highly Linear High-Power 802.11ac/ax WLAN SiGe HBT Power Amplifiers With a Compact 2nd-Harmonic-Shorted Four-Way Transformer and a Thermally Compensating Dynamic Bias Circuit. IEEE Journal of Solid-State Circuits, 2020, 55, 2356-2370.	3.5	26
38	Physics of Hot Carrier Degradation Under Saturation Mode Operation in SiGe HBTs. , 2020, , .		0
39	Circuit-Level Safe-Operating-Area of a High-Speed SiGe BiCMOS Wireline Driver. , 2020, , .		1
40	A New Wideband, Low Insertion Loss SiGe Digital Step Attenuator A New Wideband, Low Insertion Loss SiGe Digital Step Attenuator. , 2020, , .		2
41	A Compact, High-Power, 60 GHz SPDT Switch Using Shunt-Series SiGe PIN Diodes. , 2019, , .		6
42	Total Ionizing Dose Effects in 70-GHz Bandwidth Photodiodes in a SiGe Integrated Photonics Platform. IEEE Transactions on Nuclear Science, 2019, 66, 125-133.	1.2	11
43	High energy swift heavy ion irradiation and annealing effects on DC electrical characteristics of 200ÅGHz SiGe HBTs. Nuclear Engineering and Technology, 2019, 51, 1428-1435.	1.1	9
44	DC and RF Variability of SiGe HBTs Operating Down to Deep Cryogenic Temperatures. , 2019, , .		6
45	Reliability Differences Between SiGe HBTs Optimized for High-Performance and Medium-Breakdown. , 2019, , .		1
46	A 2-20 GHz SiGe Amplitude Control Circuit with Differential Signal Selectivity for Wideband Reconfigurable Electronics. , 2019, , .		1
47	Optimizing Optical Parameters to Facilitate Correlation of Laser- and Heavy-Ion-Induced Single-Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2019, 66, 359-367.	1.2	15
48	The Effects of Temperature on the Single-Event Transient Response of a High-Voltage (>30 V) Complementary SiGe-on-SOI Technology. IEEE Transactions on Nuclear Science, 2019, 66, 389-396.	1.2	1
49	Best Practices for Using Electrostatic Discharge Protection Techniques for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2019, 66, 240-247.	1.2	3
50	Using Bessel beams and two-photon absorption to predict radiation effects in microelectronics. Optics Express, 2019, 27, 37652.	1.7	9
51	Single-Event Upset Mitigation in a Complementary SiGe HBT BiCMOS Technology. IEEE Transactions on Nuclear Science, 2018, 65, 231-238.	1.2	7
52	Limiting Effects on the Design of Vertical Superjunction Collectors in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 793-797.	1.6	0
53	A Highly Efficient X-Band Inverse Class-F SiGe HBT Cascode Power Amplifier With Harmonic-Tuned Wilkinson Power Combiner. IEEE Transactions on Circuits and Systems II: Express Briefs, 2018, 65, 1609-1613.	2.2	16
54	p-n-p-Based RF Switches for the Mitigation of Single-Event Transients in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2018, 65, 391-398.	1.2	6

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55	Utilizing SiGe HBT Power Detectors for Sensing Single-Event Transients in RF Circuits. IEEE Transactions on Nuclear Science, 2018, 65, 239-248.	1.2	8
56	An Electrostatic Discharge Protection Circuit Technique for the Mitigation of Single-Event Transients in SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2018, 65, 426-431.	1.2	4
57	Design and Analysis of a Low Loss, Wideband Digital Step Attenuator With Minimized Amplitude and Phase Variations. IEEE Journal of Solid-State Circuits, 2018, 53, 2202-2213.	3.5	57
58	Hot-Carrier-Damage-Induced Current Gain Enhancement (CGE) Effects in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 2430-2438.	1.6	11
59	Experimental Validation of an Equivalent LET Approach for Correlating Heavy-Ion and Laser-Induced Charge Deposition. IEEE Transactions on Nuclear Science, 2018, 65, 1724-1733.	1.2	25
60	A Compact Highly Efficient High-Power Ka-band SiGe HBT Cascode Frequency Doubler With Four-Way Input Transformer Balun. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 2879-2887.	2.9	19
61	Cryogenic Characterization of RF Low-Noise Amplifiers Utilizing Inverse-Mode SiGe HBTs for Extreme Environment Applications. IEEE Transactions on Device and Materials Reliability, 2018, 18, 613-619.	1.5	0
62	A \$Ka\$ -Band SiGe Bootstrapped Gilbert Frequency Doubler With 26.2% PAE. IEEE Microwave and Wireless Components Letters, 2018, 28, 1122-1124.	2.0	9
63	Revisiting Safe Operating Area: SiGe HBT Aging Models for Reliability-Aware Circuit Design. , 2018, , .		2
64	A V-Band SiGe Image-Reject Receiver Front-End for Atmospheric Remote Sensing. , 2018, , .		6
65	Using SiGe-on-SOI HBTs to Build 300Å°C Capable Analog Circuits. , 2018, , .		1
66	Emitter-Base Profile Optimization of SiGe HBTs for Improved Thermal Stability and Frequency Response at Low-Bias Currents. , 2018, , .		1
67	A Low-Loss Broadband Quadrature Signal Generation Network for High Image Rejection at Millimeter-Wave Frequencies. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 5336-5346.	2.9	13
68	A SiGe-BiCMOS Wideband Active Bidirectional Digital Step Attenuator With Bandwidth Tuning and Equalization. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 3866-3876.	2.9	13
69	Collector Transport in SiGe HBTs Operating at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2018, 65, 3697-3703.	1.6	15
70	Potential Limitations on Integrated Silicon Photonic Waveguides Operating in a Heavy Ion Environment. IEEE Transactions on Nuclear Science, 2018, 65, 141-148.	1.2	18
71	SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406.	1.2	9
72	A True Time Delay-based SiGe Bi-directional T/R Chipset for Large-Scale Wideband Timed Array Antennas. , 2018, , .		22

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73	Next Generation of Automotive Radar with Leading-Edge Advances in SiGe Devices and Glass Panel Embedding (GPE). , 2018, , .		5
74	On the Application of Inverse-Mode SiGe HBTs in RF Receivers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 1142-1150.	1.2	9
75	Modeling Single-Event Transient Propagation in a SiGe BiCMOS Direct-Conversion Receiver. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	6
76	A 0.3â€“15 GHz SiGe LNA With >1 THz Gain-Bandwidth Product. IEEE Microwave and Wireless Components Letters, 2017, 27, 380-382.	2.0	11
77	Operation of SiGe HBTs Down to 70 mK. IEEE Electron Device Letters, 2017, 38, 12-15.	2.2	28
78	Single-Event Effects in High-Frequency Linear Amplifiers: Experiment and Analysis. IEEE Transactions on Nuclear Science, 2017, 64, 125-132.	1.2	5
79	The Impact of Technology Scaling on the Single-Event Transient Response of SiGe HBTs. IEEE Transactions on Nuclear Science, 2017, 64, 406-414.	1.2	22
80	Physical Differences in Hot Carrier Degradation of Oxide Interfaces in Complementary (n-p-n+p-n-p) SiGe HBTs. IEEE Transactions on Electron Devices, 2017, 64, 37-44.	1.6	10
81	Using TCAD Modeling to Compare Heavy-Ion and Laser-Induced Single Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2017, 64, 398-405.	1.2	24
82	Single-Event Effects in a Millimeter-Wave Receiver Front-End Implemented in 90 nm, 300 GHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2017, 64, 536-543.	1.2	5
83	An X-band inverse class-F SiGe HBT cascode power amplifier With harmonic-tuned output transformer. , 2017, , .		12
84	An Investigation of High-Temperature (to 300 Â°C) Safe-Operating-Area in a High-Voltage Complementary SiGe on SOI Technology. IEEE Transactions on Electron Devices, 2017, 64, 3748-3755.	1.6	5
85	A bi-directional, X-band 6-Bit phase shifter for phased array antennas using an active DPDT switch. , 2017, , .		4
86	Total Ionizing Dose Effects on a High-Voltage (>30V) Complementary SiGe on SOI Technology. IEEE Transactions on Nuclear Science, 2017, 64, 277-284.	1.2	5
87	Single-Event Transient Response of Comparator Pre-Amplifiers in a Complementary SiGe Technology. IEEE Transactions on Nuclear Science, 2017, 64, 89-96.	1.2	8
88	The Use of Inverse-Mode SiGe HBTs as Active Gain Stages in Low-Noise Amplifiers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 359-366.	1.2	8
89	The effects of total ionizing dose on the transient response of SiGe BiCMOS technologies. , 2016, , .		1
90	Modeling single-event transient propagation in a SiGe BiCMOS direct-conversion receiver. , 2016, , .		1

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91	SiGe Technology as a Millimeter-Wave Platform: Scaling Issues, Reliability Physics, Circuit Performance, and New Opportunities. , 2016, , .		5
92	A SiGe-BiCMOS Wideband (2â€“22 GHz) Active Power Divider/Combiner Circuit Supporting Bidirectional Operation. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 4676-4684.	2.9	12
93	An Investigation of the Use of Inverse-Mode SiGe HBTs as Switching Pairs for SET-Mitigated RF Mixers. IEEE Transactions on Nuclear Science, 2016, 63, 1099-1108.	1.2	13
94	A Compact, Wideband Lumped-Element Wilkinson Power Divider/Combiner Using Symmetric Inductors with Embedded Capacitors. IEEE Microwave and Wireless Components Letters, 2016, 26, 595-597.	2.0	19
95	Design and On-Wafer Characterization of \$G\$ -Band SiGe HBT Low-Noise Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 3631-3642.	2.9	27
96	Inverse classâ€“Fâ€“band â€“Sâ€“iâ€“Gâ€“e â€“HBTâ€“ power amplifier with 44% â€“PAEâ€“ and 24.5 dâ€“Bâ€“m peak output power. Microwave and Optical Technology Letters, 2016, 58, 2868-2871.	0.9	1
97	On the use of vertical superjunction collectors for enhanced breakdown performance in SiGe HBTs. , 2016, , .		4
98	Wideband active bi-directional SiGe digital step attenuator using an active DPDT switch. , 2016, , .		1
99	Modeling of high-current damage in SiGe HBTs under pulsed stress. , 2016, , .		3
100	Beyond the boundaries: Enabling new circuit opportunities by using SiGe HBTs in counterintuitive ways. , 2016, , .		2
101	A Physics-Based Circuit Aging Model for Mixed-Mode Degradation in SiGe HBTs. IEEE Transactions on Electron Devices, 2016, 63, 2987-2993.	1.6	15
102	An Active Bi-Directional SiGe DPDT Switch With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 279-281.	2.0	13
103	An Investigation of Single-Event Effect Modeling Techniques for a SiGe RF Low-Noise Amplifier. IEEE Transactions on Nuclear Science, 2016, 63, 273-280.	1.2	16
104	Wide temperature range SiGe HBT noise parameter modeling and LNA design for extreme environment Electronics. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2015, 28, 675-683.	1.2	5
105	Optimization of SiGe HBT RF Switches for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2015, 62, 3057-3063.	1.2	8
106	An Investigation of the SET Response of Devices and Differential Pairs in a 32-nm SOI CMOS Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2643-2649.	1.2	1
107	Optimizing the vertical profile of SiGe HBTs to mitigate radiation-induced upsets. , 2015, , .		5
108	Single-Event Effects in a W-Band (75-110â€“GHz) Radar Down-Conversion Mixer Implemented in 90â€“nm, 300â€“GHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2657-2665.	1.2	12

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109	The Role of Negative Feedback Effects on Single-Event Transients in SiGe HBT Analog Circuits. IEEE Transactions on Nuclear Science, 2015, 62, 2599-2605.	1.2	4
110	A SiGe D-Band Low-Noise Amplifier Utilizing Gain-Boosting Technique. IEEE Microwave and Wireless Components Letters, 2015, 25, 61-63.	2.0	35
111	On the Cryogenic RF Linearity of SiGe HBTs in a Fourth-Generation 90-nm SiGe BiCMOS Technology. IEEE Transactions on Electron Devices, 2015, 62, 1127-1135.	1.6	5
112	Bias- and Temperature-Dependent Accumulated Stress Modeling of Mixed-Mode Damage in SiGe HBTs. IEEE Transactions on Electron Devices, 2015, 62, 2084-2091.	1.6	19
113	A Comparison of Field and Current-Driven Hot-Carrier Reliability in NPN SiGe HBTs. IEEE Transactions on Electron Devices, 2015, 62, 2244-2250.	1.6	19
114	Large-Signal Reliability Analysis of SiGe HBT Cascode Driver Amplifiers. IEEE Transactions on Electron Devices, 2015, 62, 1383-1389.	1.6	28
115	A Comparison of the Degradation in RF Performance Due to Device Interconnects in Advanced SiGe HBT and CMOS Technologies. IEEE Transactions on Electron Devices, 2015, 62, 1803-1810.	1.6	50
116	The reliability studies of nano-engineered SiGe HBTs using Pelletron accelerator. AIP Conference Proceedings, 2015, , .	0.3	1
117	A Class-E Tuned W-Band SiGe Power Amplifier With 40.4% Power-Added Efficiency at 93 GHz. IEEE Microwave and Wireless Components Letters, 2015, 25, 663-665.	2.0	26
118	A W-band integrated silicon-germanium loop-back and front-end transmit-receive switch for Built-in-self-test. , 2015, , .		4
119	Hot-Carrier Degradation in Silicon-Germanium Heterojunction Bipolar Transistors. , 2015, , 371-398.		4
120	80 MeV Carbon Ion Irradiation Effects On Advanced 200 GHz Silicon-germanium Heterojunction Bipolar Transistors. Advanced Materials Letters, 2015, 6, 120-126.	0.3	7
121	Impact of Total Ionizing Dose on a 4th Generation, 90Ånm SiGe HBT Gaussian Pulse Generator. IEEE Transactions on Nuclear Science, 2014, 61, 3050-3054.	1.2	10
122	Single-Event Transient and Total Dose Response of Precision Voltage Reference Circuits Designed in a 90-nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2014, 61, 3210-3217.	1.2	22
123	W-band SiGe power amplifiers. , 2014, , .		11
124	An Investigation of Single-Event Transients in C-SiGe HBT on SOI Current Mirror Circuits. IEEE Transactions on Nuclear Science, 2014, 61, 3193-3200.	1.2	15
125	Device-to-circuit interactions in SiGe technology: Challenges and opportunities. , 2014, , .		6
126	Development of silicon-germanium circuits for high-frequency small satellite-based integrated radiometers. , 2014, , .		1

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127	Evaluation of Enhanced Low Dose Rate Sensitivity in Fourth-Generation SiGe HBTs. IEEE Transactions on Nuclear Science, 2014, 61, 2915-2922.	1.2	18
128	On the Transient Response of a Complementary (npn & formula formulatype="inline"><tex Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 Transactions on Nuclear Science, 2014, 61, 3146-3153.	1.2	15
129	Design of Radiation-Hardened RF Low-Noise Amplifiers Using Inverse-Mode SiGe HBTs. IEEE Transactions on Nuclear Science, 2014, 61, 3218-3225.	1.2	34
130	Mitigation of Total Dose Performance Degradation in an 8â€“18ÂGHz SiGe Reconfigurable Receiver. IEEE Transactions on Nuclear Science, 2014, 61, 3226-3235.	1.2	4
131	A digitally-controlled seven-state X-band SiGe variable gain low noise amplifier. , 2014, , .		4
132	A 1.0 V, 10â€“22 GHz, 4 mW LNA Utilizing Weakly Saturated SiGe HBTs for Single-Chip, Low-Power, Remote Sensing Applications. IEEE Microwave and Wireless Components Letters, 2014, 24, 890-892.	2.0	17
133	Evaluating the Effects of Single Event Transients in FET-Based Single-Pole Double-Throw RF Switches. IEEE Transactions on Nuclear Science, 2014, 61, 756-765.	1.2	12
134	A Low-Loss and High Isolation D-Band SPDT Switch Utilizing Deep-Saturated SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2014, 24, 400-402.	2.0	37
135	On the Analysis and Design of Low-Loss Single-Pole Double-Throw W-Band Switches Utilizing Saturated SiGe HBTs. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 2755-2767.	2.9	132
136	Advanced SiGe BiCMOS Technology for Multi-Mrad Electronic Systems. IEEE Transactions on Device and Materials Reliability, 2014, 14, 844-848.	1.5	22
137	A switchable-core SiGe HBT low-noise amplifier for millimeter-wave radiometer applications. , 2014, , .		2
138	A 94 GHz, 1.4 dB Insertion Loss Single-Pole Double-Throw Switch Using Reverse-Saturated SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2014, 24, 56-58.	2.0	37
139	A SiGe 8â€“18-GHz Receiver With Built-In-Testing Capability for Self-Healing Applications. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 2370-2380.	2.9	10
140	Impact of Technology Scaling in sub-100Ânm nMOSFETs on Total-Dose Radiation Response and Hot-Carrier Reliability. IEEE Transactions on Nuclear Science, 2014, 61, 1426-1432.	1.2	15
141	Low-loss, wideband SPDT switches and switched-line phase shifter in 180-nm RF CMOS on SOI technology. , 2014, , .		21
142	A 0.8 THz \$f_{m MAX}\$ SiGe HBT Operating at 4.3 K. IEEE Electron Device Letters, 2014, 35, 151-153.	2.2	60
143	A Comparison of Hot Carrier and 50ÂMeV Li ³⁺ Ion Induced Degradation in the Electrical Characteristics of Advanced 200ÂGHz SiGe HBT. Environmental Science and Engineering, 2014, , 113-116.	0.1	0
144	An Investigation of Single Event Transient Response in 45-nm and 32-nm SOI RF-CMOS Devices and Circuits. IEEE Transactions on Nuclear Science, 2013, 60, 4405-4411.	1.2	18

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145	In situ investigation of 75 MeV boron and 100 MeV oxygen ion irradiation effects on 50 GHz silicon-germanium heterojunction bipolar transistors. Radiation Effects and Defects in Solids, 2013, 168, 620-624.	0.4	6
146	TCAD modeling of accumulated damage during time-dependent mixed-mode stress. , 2013, , .		6
147	A design methodology to achieve low input impedance and non-constant gain-bandwidth product in TIAs for optical communication. , 2013, , .		4
148	An Investigation on the Optimization and Scaling of Complementary SiGe HBTs. IEEE Transactions on Electron Devices, 2013, 60, 34-41.	1.6	4
149	Radiation Effects in SiGe Technology. IEEE Transactions on Nuclear Science, 2013, 60, 1992-2014.	1.2	127
150	Integrated, digitally controlled, 64-element SiGe on multilayer organic X-band phased-array receiver antenna for snow measurements. IEEE Aerospace and Electronic Systems Magazine, 2013, 28, 26-39.	2.3	1
151	Total Ionizing Dose Response of Triple-Well FET-Based Wideband, High-Isolation RF Switches in a 130 nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2013, 60, 2567-2573.	1.2	12
152	An Investigation of Single-Event Effects and Potential SEU Mitigation Strategies in Fourth-Generation, 90 nm SiGe BiCMOS. IEEE Transactions on Nuclear Science, 2013, 60, 4175-4183.	1.2	20
153	A compact, transformer-based 60 GHz SPDT RF switch utilizing diode-connected SiGe HBTs. , 2013, , .		11
154	Integrated silicon-germanium electronics for CubeSat-based radiometers. , 2013, , .		7
155	An on-chip SiGe HBT characterization circuit for use in self-healing RF systems. , 2013, , .		1
156	Total Dose and Transient Response of SiGe HBTs from a New 4th-Generation, 90 nm SiGe BiCMOS Technology. , 2012, , .		20
157	A new approach to designing electronic systems for operation in extreme environments: Part I - The SiGe Remote Sensor Interface. IEEE Aerospace and Electronic Systems Magazine, 2012, 27, 25-34.	2.3	11
158	An 8-16 GHz SiGe Low Noise Amplifier With Performance Tuning Capability for Mitigation of Radiation-Induced Performance Loss. IEEE Transactions on Nuclear Science, 2012, 59, 2837-2846.	1.2	31
159	An Ultra-Thin, High-Power, and Multilayer Organic Antenna Array With T/R Functionality in the X-Band. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 3856-3867.	2.9	11
160	A 6-20 GHz Adaptive SiGe Image Reject Mixer for a Self-Healing Receiver. IEEE Journal of Solid-State Circuits, 2012, 47, 1998-2006.	3.5	19
161	Single-Event Response of the SiGe HBT Operating in Inverse-Mode. IEEE Transactions on Nuclear Science, 2012, 59, 2682-2690.	1.2	23
162	A New Self-Healing Methodology for RF Amplifier Circuits Based on Oscillation Principles. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2012, 20, 1835-1848.	2.1	39

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